

In The Claims:

Cancel claims 1-10 and 17 without prejudice or disclaimer.

1-10. (Cancelled)

11.(Original) A method for manufacturing a semiconductor laser device including, on a GaAs substrate, at least a first-conductive-type lower cladding layer, a lower guide layer, a quantum well active layer composed of at least one well layer and at least two barrier layers, an upper guide layer and a second-conductive-type upper cladding layer, one on another, wherein

at least one layer out of the plurality of layers is a P-based layer formed of group III-V compound semiconductor containing P as a group V element, the method comprising the steps of:

subjecting the P-based layer to crystal growth at a first growth temperature; and above the P-based layer, starting growth of an As-based layer formed of group III-V compound semiconductor containing not P but As as a group V element at a growth temperature approximately equal to the first growth temperature, and thereafter furthering the growth while elevating the temperature to a second growth temperature.

12. (Original) The method for manufacturing a semiconductor laser device according to Claim 11, further comprising the step of: before the growth of the As-based layer, making one layer or a plurality of layers of other As-based layer grown just above the P-based layer at a temperature approximately equal to the first growth temperature.

13. (Original) The method for manufacturing a semiconductor laser device according to Claim 11, wherein the first growth temperature is not less than 600°C and not more than 680°C.

14. (Original) The method for manufacturing a semiconductor laser device according to Claim 11, wherein the second growth temperature is not less than 700°C and not more than 780°C.

15. (Original) The method for manufacturing a semiconductor laser device according to Claim 11, wherein the P-based layer is formed of InGaAsP, InGaP, GaAsP or AlGaInP.

16. (Original) The semiconductor laser device according to Claim 1, wherein the As-based layer is formed of GaAs, AlGaAs, AlAs, InGaAs or AlGaInAs.

17. (Cancelled)